

VS-15ETH06SPbF, VS-15ETH06-1PbF

Vishay Semiconductors

RoHS

HALOGEN

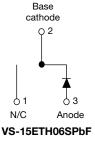
FREE

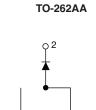
Hyperfast Rectifier, 15 A FRED Pt®





TO-263AB (D²PAK)





VS-15ETH06-1PbF

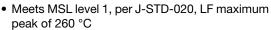
Anode

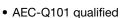
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PRODUCT SUMMARY	
Package	TO-263AB (D ² PAK), TO-262AA
I _{F(AV)}	15 A
V_{R}	600 V
V _F at I _F	1.3 V
t _{rr} (typ.)	22 ns
T _J max.	175 °C
Diode variation	Single diode

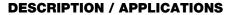
FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Single die center tap module





 Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage	V_{RRM}		600	V
Average rectified forward current	I _{F(AV)}	T _C = 140 °C	15	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	120	Α
Peak repetitive forward current	I _{FM}		30	
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	.,	
Commend welltone	V _F	I _F = 15 A	-	1.8	2.2	V	
Forward voltage	v _F	I _F = 15 A, T _J = 150 °C	-	1.3	1.6		
Reverse leakage current	I _R	$V_R = V_R$ rated	-	0.2	50	μA	
neverse leakage current	I IR	T _J = 150 °C, V _R = V _R rated	-	30	500	μΑ	
Junction capacitance	C _T	V _R = 600 V	-	20	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	



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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 10$	00 A/μs, V _R = 30 V	-	22	30	
Payersa raggiust tima		I _F = 15 A, dI _F /dt =	100 A/μs, V _R = 30 V	-	28	35	no
Reverse recovery time	t _{rr}	T _J = 25 °C		-	29	-	ns
		T _J = 125 °C	I _F = 15 A dI _F /dt = 200 A/μs V _R = 390 V	-	75	-	
Deals recovery current	I _{RRM}	T _J = 25 °C		-	3.5	-	А
Peak recovery current		T _J = 125 °C		-	7	-	
Daverse receiver charge	0	T _J = 25 °C		-	57	-	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	300	-	μC
Reverse recovery time	t _{rr}		I _F = 15 A	-	51	-	ns
Peak recovery current	I _{RRM}	T _J = 125 °C	dl _F /dt = 800 A/μs	-	20	-	Α
Reverse recovery charge	Q _{rr}]	V _R = 390 V	-	580	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	1.0	1.3	
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Waight			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking daving	Case style TO-263AB (D ² PAK)	Case style TO-263AB (D ² PAK)	15ETH06S			
Marking device		Case style TO-262AA 15ETH06			H06-1	

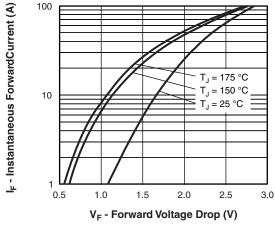


Fig. 1 - Typical Forward Voltage Drop Characteristics

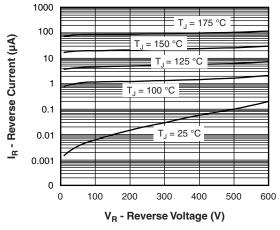


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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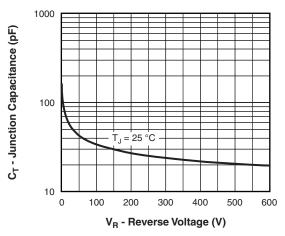


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

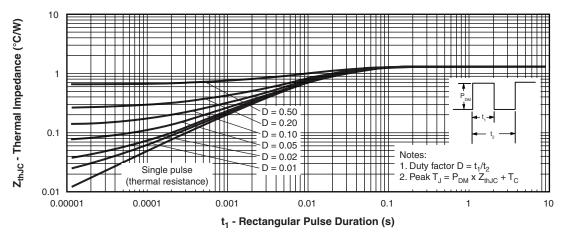


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

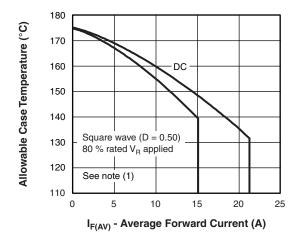


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

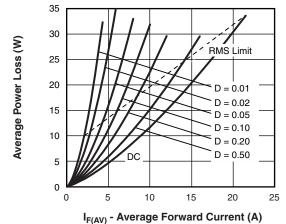


Fig. 6 - Forward Power Loss Characteristics

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}$; $Pd = Forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = Inverse power loss = V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = Rated V_R$

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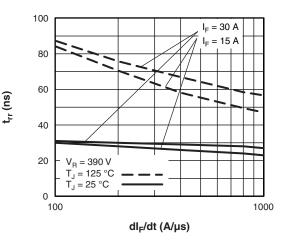


Fig. 7 - Typical Reverse Recovery vs. dl_F/dt

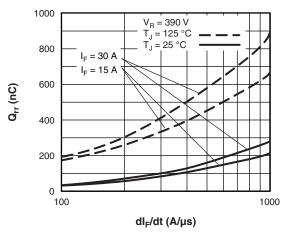
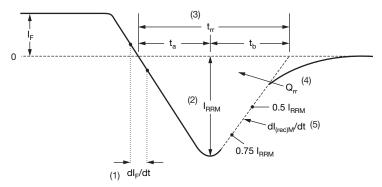


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{r}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\rm Q_{rr}$ area under curve defined by $\rm t_{rr}$ and $\rm I_{RBM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

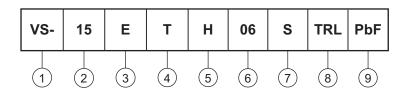
Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (15 A)

3 - E = single diode

4 - T = TO-220, D^2PAK

- H = hyperfast rectifier

Voltage rating (06 = 600 V)

7 - • S = D²PAK

• -1 = TO-262

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D²PAK package)

• TRR = tape and reel (right oriented, for D²PAK package)

9 - PbF = lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-15ETH06SPBF	50	1000	Antistatic plastic tubes			
VS-15ETH06TRRSPBF	800	800	13" diameter plastic tape and reel			
VS-15ETH06STRLPBF	800	800	13" diameter plastic tape and reel			
VS-15ETH06-1PBF	50	1000	Antistatic plastic tubes			

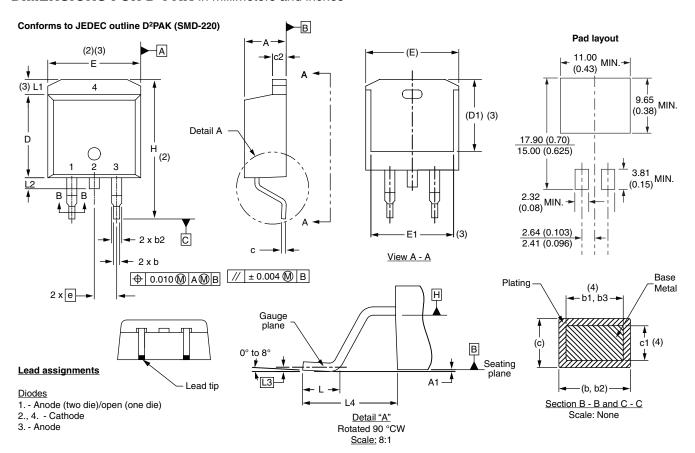
LINKS TO RELATED DOCUMENTS				
Dimensions TO-263AB (D ² PAK) <u>www.vishay.com/doc?95046</u>				
Differsions	TO-262AA	www.vishay.com/doc?95419		
Part marking information		www.vishay.com/doc?95008		
Packaging information		www.vishay.com/doc?95032		



Vishay High Power Products

D²PAK, TO-262

DIMENSIONS FOR D²PAK in millimeters and inches



	MILLIM	MILLIMETERS		INCHES	
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}\,$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch

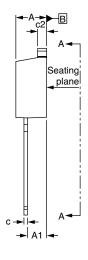
(7) Outline conforms to JEDEC outline TO-263AB

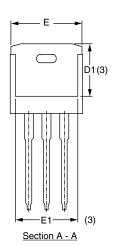
Vishay High Power Products

D²PAK, TO-262



DIMENSIONS FOR TO-262 in millimeters and inches





⊕ 0.010**⋒**|A**⋒**|B

Lead assignments

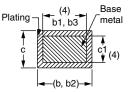


<u>Diodes</u>

-3 x b2 --3 x b

> 1. - Anode (two die)/open (one die) 2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

OVMDOL	MILLIN	METERS	INC	INCHES		
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
Е	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.10	0 BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



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Revision: 13-Jun-16 1 Document Number: 91000